

Yanhui Zhang

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

25
papers

297
citations

12
h-index

16
g-index

25
ext. papers

349
ext. citations

5
avg, IF

2.56
L-index

#	Paper	IF	Citations
25	Synthesis of large-area graphene on molybdenum foils by chemical vapor deposition. <i>Carbon</i> , 2012 , 50, 5226-5231	10.4	38
24	Invisible growth of microstructural defects in graphene chemical vapor deposition on copper foil. <i>Carbon</i> , 2016 , 96, 237-242	10.4	36
23	Temperature-dependent nitrogen configuration of N-doped graphene by chemical vapor deposition. <i>Carbon</i> , 2015 , 81, 814-820	10.4	34
22	Wrinkle-dependent hydrogen etching of chemical vapor deposition-grown graphene domains. <i>Carbon</i> , 2014 , 70, 75-80	10.4	25
21	Mechanism of SiO _x particles formation during CVD graphene growth on Cu substrates. <i>Carbon</i> , 2018 , 139, 989-998	10.4	17
20	Effect of Cu substrate roughness on growth of graphene domains at atmospheric pressure. <i>Materials Letters</i> , 2014 , 131, 138-140	3.3	17
19	Stripe distributions of graphene-coated Cu foils and their effects on the reduction of graphene wrinkles. <i>RSC Advances</i> , 2015 , 5, 96587-96592	3.7	15
18	Edge morphology evolution of graphene domains during chemical vapor deposition cooling revealed through hydrogen etching. <i>Nanoscale</i> , 2016 , 8, 4145-50	7.7	15
17	Evidence of electric field-tunable tunneling probability in graphene and metal contact. <i>Nanoscale</i> , 2017 , 9, 9520-9528	7.7	13
16	Effect of Hydrogen in Size-Limited Growth of Graphene by Atmospheric Pressure Chemical Vapor Deposition. <i>Journal of Electronic Materials</i> , 2015 , 44, 79-86	1.9	13
15	Realizing controllable graphene nucleation by regulating the competition of hydrogen and oxygen during chemical vapor deposition heating. <i>Physical Chemistry Chemical Physics</i> , 2016 , 18, 23638-42	3.6	12
14	How Do Contact and Channel Contribute to the Dirac Points in Graphene Field-Effect Transistors?. <i>Advanced Electronic Materials</i> , 2018 , 4, 1800158	6.4	12
13	High quality graphene grown on single-crystal Mo(110) thin films. <i>Materials Letters</i> , 2013 , 93, 165-168	3.3	10
12	Growth promotion of vertical graphene on SiO/Si by Ar plasma process in plasma-enhanced chemical vapor deposition.. <i>RSC Advances</i> , 2018 , 8, 18757-18761	3.7	8
11	Effects of carbon-based impurities on graphene growth. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 15419-15423	3.6	8
10	High pressure-assisted transfer of ultraclean chemical vapor deposited graphene. <i>Applied Physics Letters</i> , 2016 , 108, 132106	3.4	6
9	Improved carrier mobility of chemical vapor deposition-graphene by counter-doping with hydrazine hydrate. <i>Applied Physics Letters</i> , 2015 , 106, 091602	3.4	4

8	Thermal-assisted direct transfer of graphene onto flexible substrates. <i>Materials Letters</i> , 2018 , 229, 252-255	3.5	3
7	Role of hydrogen and oxygen in the study of substrate surface impurities and defects in the chemical vapor deposition of graphene. <i>Carbon</i> , 2021 , 185, 82-95	10.4	3
6	Chemical vapor deposition growth and characterization of graphite-like film. <i>Materials Research Express</i> , 2020 , 7, 015609	1.7	2
5	Stripe distribution on graphene-coated Cu surface and its effect on oxidation and corrosion resistance of graphene. <i>Journal of Applied Physics</i> , 2017 , 121, 245306	2.5	2
4	Enhancement of the Electrical Properties of CVD-Grown Graphene with Ascorbic Acid Treatment. <i>Journal of Electronic Materials</i> , 2016 , 45, 1160-1164	1.9	1
3	Undulate Cu(111) Substrates: A Unique Surface for CVD Graphene Growth. <i>Journal of Electronic Materials</i> , 2015 , 44, 3550-3555	1.9	1
2	A comparative study of Ge/Au/Ni/Au-based ohmic contact on graphene. <i>Journal of Semiconductors</i> , 2014 , 35, 056001	2.3	1
1	Re-nucleation and Etching of Graphene During the Cooling Stage of Chemical Vapor Deposition. <i>Journal of Electronic Materials</i> , 2019 , 48, 1740-1745	1.9	1